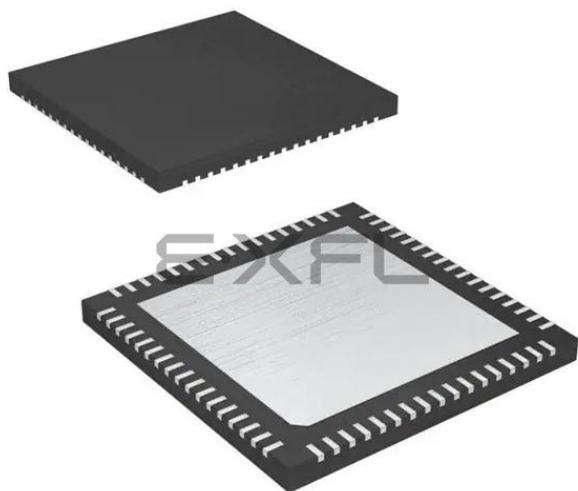




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	384
Total RAM Bits	-
Number of I/O	49
Number of Gates	15000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	68-VFQFN Exposed Pad
Supplier Device Package	68-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/agl015v5-qng68i

field upgrades with confidence that valuable intellectual property cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The IGLOO family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the IGLOO family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/communications, computing, and avionics markets.

Firm-Error Immunity

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of IGLOO flash-based FPGAs. Once it is programmed, the flash cell configuration element of IGLOO FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Advanced Flash Technology

The IGLOO family offers many benefits, including nonvolatility and reprogrammability, through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

IGLOO family FPGAs utilize design and process techniques to minimize power consumption in all modes of operation.

Advanced Architecture

The proprietary IGLOO architecture provides granularity comparable to standard-cell ASICs. The IGLOO device consists of five distinct and programmable architectural features (Figure 1-1 on page 1-4 and Figure 1-2 on page 1-4):

- Flash*Freeze technology
- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory[†]
- Extensive CCCs and PLLs[†]
- Advanced I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the IGLOO core tile as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the ProASIC[®] family of third-generation-architecture flash FPGAs.

[†] The AGL015 and AGL030 do not support PLL or SRAM.

Table 2-3 • Flash Programming Limits – Retention, Storage, and Operating Temperature¹

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T _{STG} (°C) ²	Maximum Operating Junction Temperature T _J (°C) ²
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

Notes:

1. This is a stress rating only; functional operation at any condition other than those indicated is not implied.
2. These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 on page 2-2 for device operating conditions and absolute limits.

Table 2-4 • Overshoot and Undershoot Limits¹

VCCI	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle ²	Maximum Overshoot/Undershoot ²
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. Based on reliability requirements at junction temperature at 85°C.
2. The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.
3. This table does not provide PCI overshoot/undershoot limits.

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every IGLOO device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in Figure 2-1 on page 2-4 and Figure 2-2 on page 2-5.

There are five regions to consider during power-up.

IGLOO I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points (Figure 2-1 on page 2-4 and Figure 2-2 on page 2-5).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:

Ramping up (V5 devices): 0.6 V < trip_point_up < 1.2 V

Ramping down (V5 Devices): 0.5 V < trip_point_down < 1.1 V

Ramping up (V2 devices): 0.75 V < trip_point_up < 1.05 V

Ramping down (V2 devices): 0.65 V < trip_point_down < 0.95 V

VCC Trip Point:

Ramping up (V5 devices): 0.6 V < trip_point_up < 1.1 V

Ramping down (V5 devices): 0.5 V < trip_point_down < 1.0 V

Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO Sleep Mode*

	Core Voltage	AGL015	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000	Units
VCCI/VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	1.7	1.7	μA
VCCI/VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	μA
VCCI/VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	1.9	1.9	μA
VCCI/VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	μA
VCCI/VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	2.5	2.5	μA

Note: $IDD = N_{BANKS} \times ICCI$. Values do not include I/O static contribution, which is shown in Table 2-13 on page 2-10 through Table 2-15 on page 2-11 and Table 2-16 on page 2-11 through Table 2-18 on page 2-12 (PDC6 and PDC7).

Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOO Shutdown Mode

	Core Voltage	AGL015	AGL030	Units
Typical (25°C)	1.2 V / 1.5 V	0	0	μA

Table 2-12 • Quiescent Supply Current (IDD), No IGLOO Flash*Freeze Mode¹

	Core Voltage	AGL015	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000	Units
ICCA Current²										
Typical (25°C)	1.2 V	5	6	10	13	18	25	28	42	μA
	1.5 V	14	16	20	28	44	66	82	137	μA
ICCI or IJTAG Current³										
VCCI/VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	1.7	1.7	μA
VCCI/VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	μA
VCCI/VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	1.9	1.9	μA
VCCI/VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	μA
VCCI/VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	2.5	2.5	μA

Notes:

1. $IDD = N_{BANKS} \times ICCI + ICCA$. JTAG counts as one bank when powered.
2. Includes VCC, VPUMP, and VCCPLL currents.
3. Values do not include I/O static contribution (PDC6 and PDC7).

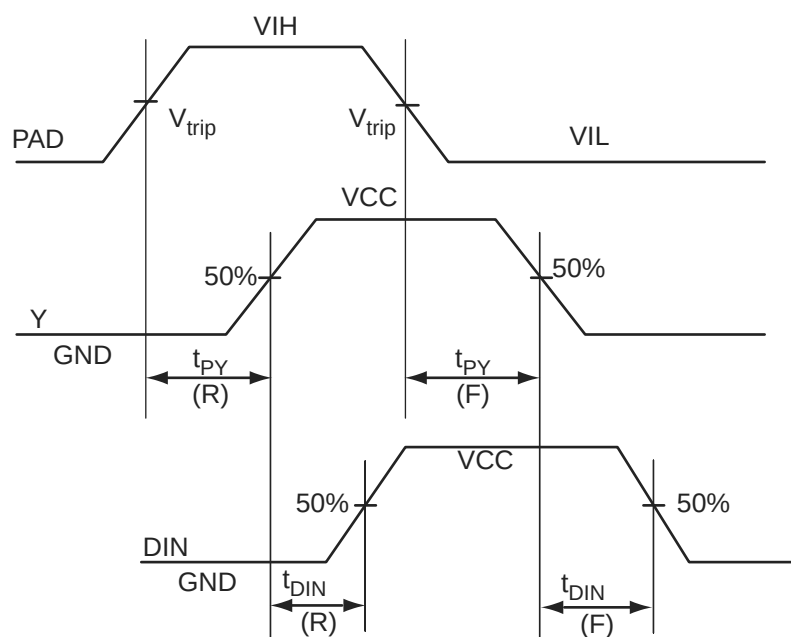
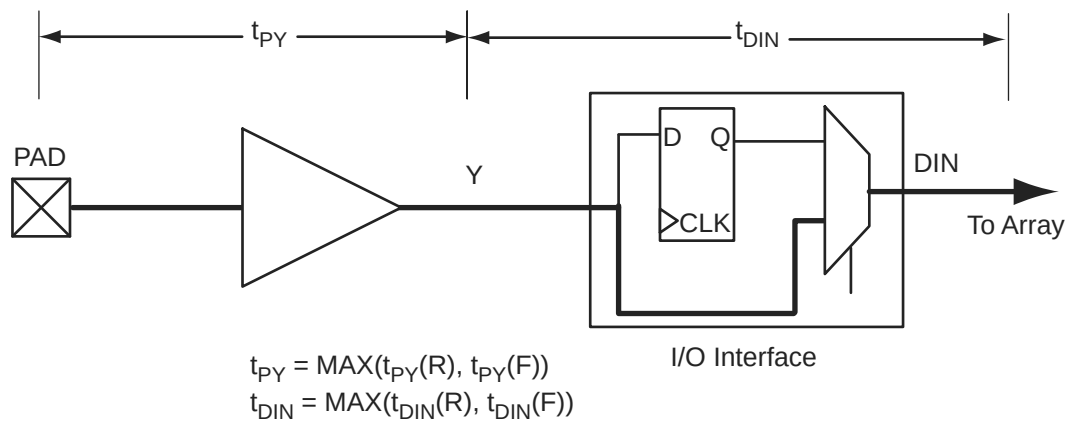


Figure 2-4 • Input Buffer Timing Model and Delays (example)

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-25 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings
Applicable to Advanced I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option ²	Slew Rate	VIL		VIH		VOL	VOH	IOL ¹	IOH ¹
				Min.V	Max. V	Min. V	Max.V	Max. V	Min. V	mA	mA
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	12 mA	High	−0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range ³	100 μ A	12 mA	High	−0.3	0.8	2	3.6	0.2	VCCI − 0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	−0.3	0.7	1.7	2.7	0.7	1.7	12	12
1.8 V LVCMOS	12 mA	12 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	12	12
1.5 V LVCMOS	12 mA	12 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	12	12
1.2 V LVCMOS ⁴	2 mA	2 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS Wide Range ^{4,5}	100 μ A	2 mA	High	−0.3	0.3 * VCCI	0.7 * VCCI	1.575	0.1	VCCI − 0.1	0.1	0.1
3.3 V PCI	Per PCI specifications										
3.3 V PCI-X	Per PCI-X specifications										

Notes:

1. Currents are measured at 85°C junction temperature.
2. The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \mu$ A. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
4. Applicable to V2 Devices operating at VCCI $\geq$ VCC.
5. All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.

Table 2-33 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case
Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case V_{CCI} (per standard)
Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option ¹ (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	8	High	5	–	0.97	1.85	0.18	0.83	0.66	1.89	1.46	1.96	2.26	ns
3.3 V LVCMOS Wide Range ²	100 μA	8	High	5	–	0.97	2.62	0.18	1.17	0.66	2.63	2.02	2.79	3.17	ns
2.5 V LVCMOS	8 mA	8	High	5	–	0.97	1.88	0.18	1.04	0.66	1.92	1.63	1.95	2.15	ns
1.8 V LVCMOS	4 mA	4	High	5	–	0.97	2.18	0.18	0.98	0.66	2.22	1.93	1.97	2.06	ns
1.5 V LVCMOS	2 mA	2	High	5	–	0.97	2.51	0.18	1.14	0.66	2.56	2.21	1.99	2.03	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-43 • I/O Short Currents IOSH/IOSL
Applicable to Standard Plus I/O Banks

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
	12 mA	103	109
	16 mA	103	109
3.3 V LVCMOS Wide Range	100 μ A	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
	12 mA	65	74
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	35	44
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
1.2 V LVCMOS	2 mA	20	26
1.2 V LVCMOS Wide Range	100 μ A	20	26
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	103	109

Note: * $T_J = 100^\circ\text{C}$

Single-Ended I/O Characteristics

3.3 V LVTTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTTL input buffer and push-pull output buffer. Furthermore, all LVCMOS 3.3 V software macros comply with LVCMOS 3.3 V wide range as specified in the JESD8a specification.

Table 2-47 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	−0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10
12 mA	−0.3	0.8	2	3.6	0.4	2.4	12	12	103	109	10	10
16 mA	−0.3	0.8	2	3.6	0.4	2.4	16	16	132	127	10	10
24 mA	−0.3	0.8	2	3.6	0.4	2.4	24	24	268	181	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-48 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	−0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10
12 mA	−0.3	0.8	2	3.6	0.4	2.4	12	12	103	109	10	10
16 mA	−0.3	0.8	2	3.6	0.4	2.4	16	16	103	109	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-60 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	2.89	0.26	0.97	1.10	2.93	2.38	2.53	2.96	8.72	8.17	ns
4 mA	Std.	1.55	2.89	0.26	0.97	1.10	2.93	2.38	2.53	2.96	8.72	8.17	ns
6 mA	Std.	1.55	2.50	0.26	0.97	1.10	2.54	2.04	2.77	3.37	8.33	7.82	ns
8 mA	Std.	1.55	2.50	0.26	0.97	1.10	2.54	2.04	2.77	3.37	8.33	7.82	ns
12 mA	Std.	1.55	2.31	0.26	0.97	1.10	2.34	1.86	2.93	3.64	8.12	7.65	ns
16 mA	Std.	1.55	2.31	0.26	0.97	1.10	2.34	1.86	2.93	3.64	8.12	7.65	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-61 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	4.39	0.26	0.94	1.10	4.46	3.91	2.17	2.44	ns
4 mA	Std.	1.55	4.39	0.26	0.94	1.10	4.46	3.91	2.17	2.44	ns
6 mA	Std.	1.55	3.72	0.26	0.94	1.10	3.78	3.43	2.40	2.85	ns
8 mA	Std.	1.55	3.72	0.26	0.94	1.10	3.78	3.43	2.40	2.85	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-62 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	2.74	0.26	0.94	1.10	2.78	2.26	2.17	2.55	ns
4 mA	Std.	1.55	2.74	0.26	0.94	1.10	2.78	2.26	2.17	2.55	ns
6 mA	Std.	1.55	2.38	0.26	0.94	1.10	2.41	1.92	2.40	2.96	ns
8 mA	Std.	1.55	2.38	0.26	0.94	1.10	2.41	1.92	2.40	2.96	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

3.3 V LVC MOS Wide Range

Table 2-63 • Minimum and Maximum DC Input and Output Levels for LVC MOS 3.3 V Wide Range
Applicable to Advanced I/O Banks

3.3 V LVC MOS Wide Range		VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ²	IIH ³
Drive Strength	Equivalent Software Default Drive Strength Option ¹	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	μA	μA	Max. mA ⁴	Max. mA ⁴	μA^5	μA^5
100 μA	2 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	25	27	10	10
100 μA	4 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	25	27	10	10
100 μA	6 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	51	54	10	10
100 μA	8 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	51	54	10	10
100 μA	12 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	103	109	10	10
100 μA	16 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	132	127	10	10
100 μA	24 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	268	181	10	10

Notes:

1. The minimum drive strength for any LVC MOS 3.3 V software configuration when run in wide range is $\pm 100 \mu\text{A}$. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3 \text{ V} < V_{\text{IN}} < V_{\text{IL}}$.
3. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{\text{IH}} < V_{\text{IN}} < V_{\text{CCI}}$. Input current is larger when operating outside recommended ranges
4. Currents are measured at 100°C junction temperature and maximum voltage.
5. Currents are measured at 85°C junction temperature.
6. Software default selection highlighted in gray.

1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

Table 2-95 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	2	2	9	11	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	4	4	17	22	10	10
6 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	6	6	35	44	10	10
8 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	8	8	45	51	10	10
12 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	12	12	91	74	10	10
16 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	16	16	91	74	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-96 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	2	2	9	11	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	4	4	17	22	10	10
6 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	6	6	35	44	10	10
8 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	8	8	35	44	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Output Enable Register

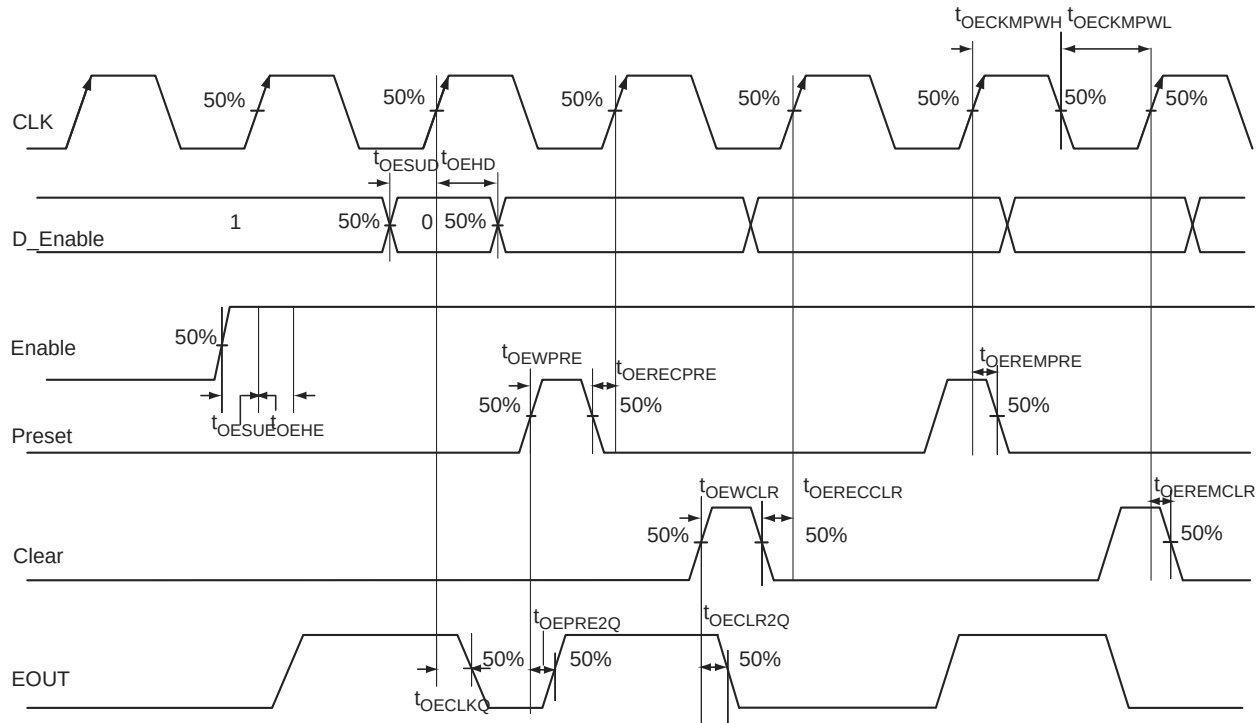


Figure 2-20 • Output Enable Register Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-161 • Output Enable Register Propagation Delays

Commercial-Case Conditions: $T_j = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.75	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.51	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.73	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	1.13	ns
t_{OEPR2Q}	Asynchronous Preset-to-Q of the Output Enable Register	1.13	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
$t_{OEWCCLR}$	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OEWPRES}$	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

DDR Module Specifications

Input DDR Module

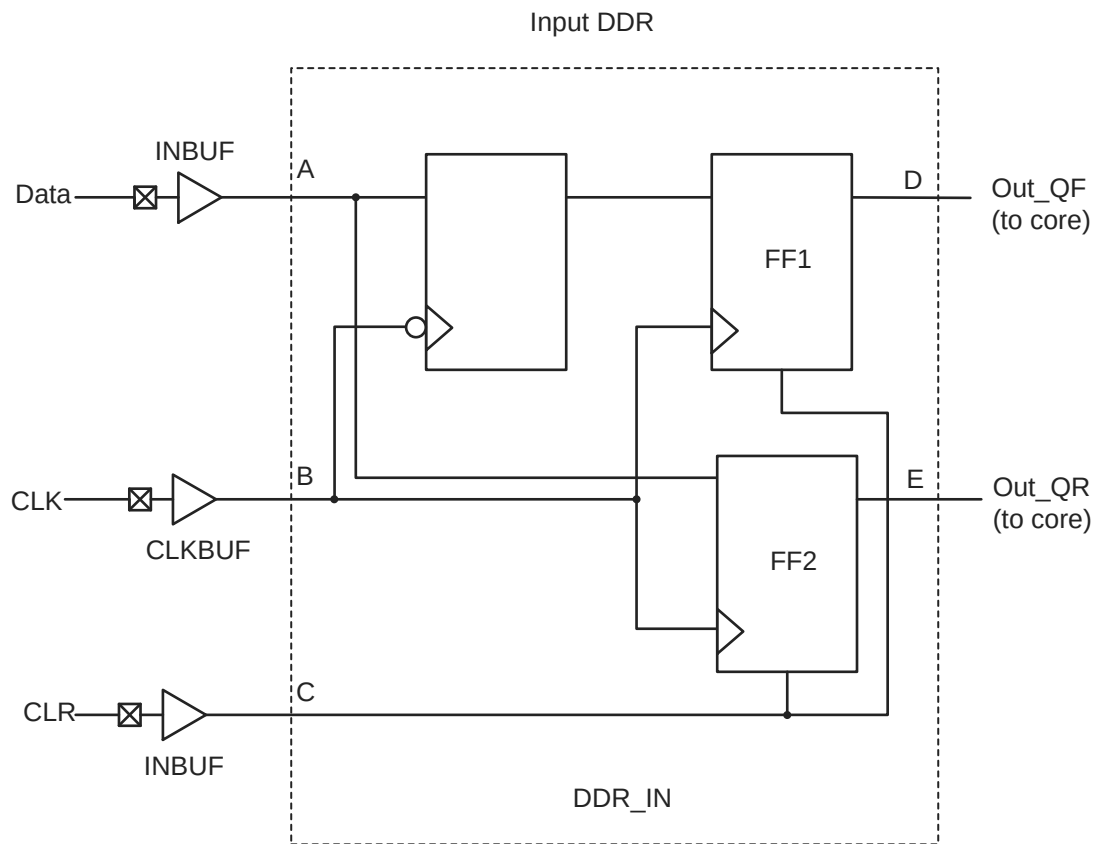


Figure 2-21 • Input DDR Timing Model

Table 2-163 • Parameter Definitions

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
t _{DDRICKQ1}	Clock-to-Out Out_QR	B, D
t _{DDRICKQ2}	Clock-to-Out Out_QF	B, E
t _{DDRISUD}	Data Setup Time of DDR input	A, B
t _{DDRIHD}	Data Hold Time of DDR input	A, B
t _{DDRICKR2Q1}	Clear-to-Out Out_QR	C, D
t _{DDRICKR2Q2}	Clear-to-Out Out_QF	C, E
t _{DDRIREMCLR}	Clear Removal	C, B
t _{DDRIRECCLR}	Clear Recovery	C, B

Timing Characteristics**1.5 V DC Core Voltage****Table 2-195 • FIFO****Worst Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$**

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.99	ns
t_{ENH}	REN, WEN Hold Time	0.16	ns
t_{BKS}	BLK Setup Time	0.30	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.76	ns
t_{DH}	Input Data (WD) Hold Time	0.25	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	3.33	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.80	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	3.53	ns
t_{WCKFF}	WCLK High to Full Flag Valid	3.35	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	12.85	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	3.48	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	12.72	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	2.02	ns
	RESET Low to Data Out Low on RD (pipelined)	2.02	ns
t_{REMRSTB}	RESET Removal	0.61	ns
t_{RECRSTB}	RESET Recovery	3.21	ns
t_{MPWRSTB}	RESET Minimum Pulse Width	0.68	ns
t_{CYC}	Clock Cycle Time	6.24	ns
F_{MAX}	Maximum Frequency for FIFO	160	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

CS196	
Pin Number	AGL400 Function
A1	GND
A2	GAA0/IO00RSB0
A3	GAC0/IO04RSB0
A4	GAC1/IO05RSB0
A5	IO14RSB0
A6	IO18RSB0
A7	IO26RSB0
A8	IO29RSB0
A9	IO36RSB0
A10	GBC0/IO54RSB0
A11	GBB0/IO56RSB0
A12	GBB1/IO57RSB0
A13	GBA1/IO59RSB0
A14	GND
B1	VCCIB3
B2	VMV0
B2	VMV0
B3	GAA1/IO01RSB0
B4	GAB1/IO03RSB0
B5	GND
B6	IO17RSB0
B7	IO25RSB0
B8	IO34RSB0
B9	IO39RSB0
B10	GND
B11	GBC1/IO55RSB0
B12	GBA0/IO58RSB0
B13	GBA2/IO60PPB1
B14	GBB2/IO61PDB1
C1	GAC2/IO153UDB3
C2	GAB2/IO154UDB3
C3	GNDQ
C4	VCCIB0
C5	GAB0/IO02RSB0
C6	IO15RSB0
C7	VCCIB0

CS196	
Pin Number	AGL400 Function
C8	IO31RSB0
C9	IO44RSB0
C10	IO49RSB0
C11	VCCIB0
C12	IO60NPB1
C13	GNDQ
C14	IO61NDB1
D1	IO153VDB3
D2	IO154VDB3
D3	GAA2/IO155UDB3
D4	IO150PPB3
D5	IO11RSB0
D6	IO20RSB0
D7	IO23RSB0
D8	IO28RSB0
D9	IO41RSB0
D10	IO47RSB0
D11	IO63PPB1
D12	VMV1
D13	IO62NDB1
D14	GBC2/IO62PDB1
E1	IO149PDB3
E2	GND
E3	IO155VDB3
E4	VCCIB3
E5	IO151USB3
E6	IO09RSB0
E7	IO12RSB0
E8	IO32RSB0
E9	IO46RSB0
E10	IO51RSB0
E11	VCCIB1
E12	IO63NPB1
E13	GND
E14	IO64PDB1
F1	IO149NDB3

CS196	
Pin Number	AGL400 Function
F2	IO144NPB3
F3	IO148PDB3
F4	IO148NDB3
F5	IO150NPB3
F6	IO07RSB0
F7	VCC
F8	VCC
F9	IO43RSB0
F10	IO73PDB1
F11	IO73NDB1
F12	IO66NDB1
F13	IO66PDB1
F14	IO64NDB1
G1	GFB1/IO146PDB3
G2	GFA0/IO145NDB3
G3	GFA2/IO144PPB3
G4	VCOMPLF
G5	GFC0/IO147NDB3
G6	VCC
G7	GND
G8	GND
G9	VCC
G10	GCC0/IO67NDB1
G11	GCB1/IO68PDB1
G12	GCA0/IO69NDB1
G13	IO72NDB1
G14	GCC2/IO72PDB1
H1	GFB0/IO146NDB3
H2	GFA1/IO145PDB3
H3	VCCPLF
H4	GFB2/IO143PPB3
H5	GFC1/IO147PDB3
H6	VCC
H7	GND
H8	GND
H9	VCC

CS281	
Pin Number	AGL1000 Function
R15	IO122RSB2
R16	GDA1/IO113PPB1
R18	GDB0/IO112NPB1
R19	GDC0/IO111NPB1
T1	IO197PPB3
T2	GEC0/IO190NPB3
T4	GEB0/IO189NPB3
T5	IO181RSB2
T6	IO172RSB2
T7	IO171RSB2
T8	IO156RSB2
T9	IO159RSB2
T10	GND
T11	IO139RSB2
T12	IO138RSB2
T13	IO129RSB2
T14	IO123RSB2
T15	GDC2/IO116RSB2
T16	TMS
T18	VJTAG
T19	GDB1/IO112PPB1
U1	IO193PDB3
U2	GEA1/IO188PPB3
U6	IO167RSB2
U14	IO128RSB2
U18	TRST
U19	GDA0/IO113NPB1
V1	IO193NDB3
V2	VCCIB3
V3	GEC2/IO185RSB2
V4	IO182RSB2
V5	IO175RSB2
V6	GND
V7	IO161RSB2
V8	IO143RSB2
V9	IO146RSB2

CS281	
Pin Number	AGL1000 Function
V10	IO145RSB2
V11	IO144RSB2
V12	IO134RSB2
V13	IO133RSB2
V14	GND
V15	IO119RSB2
V16	GDA2/IO114RSB2
V17	TDI
V18	VCCIB2
V19	TDO
W1	GND
W2	FF/GEB2/IO186RSB2
W3	IO183RSB2
W4	IO176RSB2
W5	IO170RSB2
W6	IO162RSB2
W7	IO157RSB2
W8	IO152RSB2
W9	IO149RSB2
W10	VCCIB2
W11	IO140RSB2
W12	IO135RSB2
W13	IO130RSB2
W14	IO125RSB2
W15	IO120RSB2
W16	IO118RSB2
W17	GDB2/IO115RSB2
W18	TCK
W19	GND

VQ100	
Pin Number	AGL250 Function
1	GND
2	GAA2/IO118UDB3
3	IO118VDB3
4	GAB2/IO117UDB3
5	IO117VDB3
6	GAC2/IO116UDB3
7	IO116VDB3
8	IO112PSB3
9	GND
10	GFB1/IO109PDB3
11	GFB0/IO109NDB3
12	VCOMPLF
13	GFA0/IO108NPB3
14	VCCPLF
15	GFA1/IO108PPB3
16	GFA2/IO107PSB3
17	VCC
18	VCCIB3
19	GFC2/IO105PSB3
20	GEC1/IO100PDB3
21	GEC0/IO100NDB3
22	GEA1/IO98PDB3
23	GEA0/IO98NDB3
24	VMV3
25	GNDQ
26	GEA2/IO97RSB2
27	FF/GE2/IO96RSB2
28	GEC2/IO95RSB2
29	IO93RSB2
30	IO92RSB2
31	IO91RSB2
32	IO90RSB2
33	IO88RSB2
34	IO86RSB2
35	IO85RSB2
36	IO84RSB2

VQ100	
Pin Number	AGL250 Function
37	VCC
38	GND
39	VCCIB2
40	IO77RSB2
41	IO74RSB2
42	IO71RSB2
43	GDC2/IO63RSB2
44	GDB2/IO62RSB2
45	GDA2/IO61RSB2
46	GNDQ
47	TCK
48	TDI
49	TMS
50	VMV2
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO60USB1
58	GDC0/IO58VDB1
59	GDC1/IO58UDB1
60	IO52NDB1
61	GCB2/IO52PDB1
62	GCA1/IO50PDB1
63	GCA0/IO50NDB1
64	GCC0/IO48NDB1
65	GCC1/IO48PDB1
66	VCCIB1
67	GND
68	VCC
69	IO43NDB1
70	GBC2/IO43PDB1
71	GBB2/IO42PSB1
72	IO41NDB1

VQ100	
Pin Number	AGL250 Function
73	GBA2/IO41PDB1
74	VMV1
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO29RSB0
83	IO27RSB0
84	IO25RSB0
85	IO23RSB0
86	IO21RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	GAC1/IO05RSB0
94	GAC0/IO04RSB0
95	GAB1/IO03RSB0
96	GAB0/IO02RSB0
97	GAA1/IO01RSB0
98	GAA0/IO00RSB0
99	GNDQ
100	VMV0

FG484	
Pin Number	AGL600 Function
E13	IO38RSB0
E14	IO42RSB0
E15	GBC1/IO55RSB0
E16	GBB0/IO56RSB0
E17	IO52RSB0
E18	GBA2/IO60PDB1
E19	IO60NDB1
E20	GND
E21	NC
E22	NC
F1	NC
F2	NC
F3	NC
F4	IO173NDB3
F5	IO174NDB3
F6	VMV3
F7	IO07RSB0
F8	GAC0/IO04RSB0
F9	GAC1/IO05RSB0
F10	IO20RSB0
F11	IO24RSB0
F12	IO33RSB0
F13	IO39RSB0
F14	IO44RSB0
F15	GBC0/IO54RSB0
F16	IO51RSB0
F17	VMV0
F18	IO61NPB1
F19	IO63PDB1
F20	NC
F21	NC
F22	NC
G1	IO170NDB3
G2	IO170PDB3
G3	NC
G4	IO171NDB3

FG484	
Pin Number	AGL600 Function
M3	IO158NPB3
M4	GFA2/IO161PPB3
M5	GFA1/IO162PDB3
M6	VCCPLF
M7	IO160NDB3
M8	GFB2/IO160PDB3
M9	VCC
M10	GND
M11	GND
M12	GND
M13	GND
M14	VCC
M15	GCB2/IO73PPB1
M16	GCA1/IO71PPB1
M17	GCC2/IO74PPB1
M18	IO80PPB1
M19	GCA2/IO72PDB1
M20	IO79PPB1
M21	IO78PPB1
M22	NC
N1	IO154NDB3
N2	IO154PDB3
N3	NC
N4	GFC2/IO159PDB3
N5	IO161NPB3
N6	IO156PPB3
N7	IO129RSB2
N8	VCCIB3
N9	VCC
N10	GND
N11	GND
N12	GND
N13	GND
N14	VCC
N15	VCCIB1
N16	IO73NPB1

FG484	
Pin Number	AGL600 Function
N17	IO80NPB1
N18	IO74NPB1
N19	IO72NDB1
N20	NC
N21	IO79NPB1
N22	NC
P1	NC
P2	IO153PDB3
P3	IO153NDB3
P4	IO159NDB3
P5	IO156NPB3
P6	IO151PPB3
P7	IO158PPB3
P8	VCCIB3
P9	GND
P10	VCC
P11	VCC
P12	VCC
P13	VCC
P14	GND
P15	VCCIB1
P16	GDB0/IO87NPB1
P17	IO85NDB1
P18	IO85PDB1
P19	IO84PDB1
P20	NC
P21	IO81PDB1
P22	NC
R1	NC
R2	NC
R3	VCC
R4	IO150PDB3
R5	IO151NPB3
R6	IO147NPB3
R7	GEC0/IO146NPB3
R8	VMV3